TEXAS INSTRUMENTS

Data sheet acquired from Harris Semiconductor
SCHS182

November 1997

CD74HC373, CD74HCT373, CD54HC573, CD74HC573, CD74HCT573

High Speed CMOS Logic
Octal Transparent Latch, Three-State Output

Features

- Common Latch Enable Control
- Common Three-State Output Enable Control
- Buffered Inputs
- Three-State Outputs
- Bus Line Driving Capacity
- Typical Propagation Delay = 12ns at V_{CC} = 5V, C_L = 15pF, T_A = 25^oC (Data to Output for HC373)
- Fanout (Over Temperature Range)
  - Standard Outputs . . . . . 10 LSTTL Loads
  - Bus Driver Outputs . . . . . 15 LSTTL Loads
- Wide Operating Temperature Range . . . -55^oC to 125^oC
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- HC Types
  - 2V to 6V Operation
  - High Noise Immunity: N_{IL} = 30%, N_{IH} = 30% of V_{CC} at V_{CC} = 5V
- HCT Types
  - 4.5V to 5.5V Operation
  - Direct LSTTL Input Logic Compatibility, V_{IL}= 0.8V (Max), V_{IH} = 2V (Min)
  - CMOS Input Compatibility, $I_I \leq 1\mu A$ at V_{OL}, V_{OH}

Description

The Harris CD74HC373, CD74HCT373, CD54HC573, CD74HC573, and CD74HCT573 are high speed Octal Transparent Latches manufactured with silicon gate CMOS technology. They possess the low power consumption of standard CMOS integrated circuits, as well as the ability to drive 15 LSTTL devices. The CD74HCT373 and CD74HCT573 are functionally as well as pin compatible with the standard 74LS373 and 74LS573.

The outputs are transparent to the inputs when the latch enable ($\overline{LE}$) is high. When the latch enable ($\overline{LE}$) goes low the data is latched. The output enable ($\overline{OE}$) controls the three-state outputs. When the output enable ($\overline{OE}$) is high the outputs are in the high impedance state. The latch operation is independent to the state of the output enable. The 373 and 573 are identical in function and differ only in their pinout arrangements.

Ordering Information

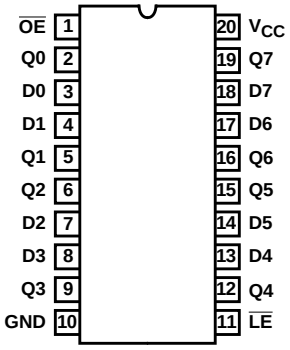
PART NUMBER	TEMP. RANGE (^oC)	PACKAGE	PKG. NO.
CD54HC573F	-55 to 125	20 Ld CERDIP	F20.3
CD74HC373E	-55 to 125	20 Ld PDIP	F20.3
CD74HCT373E	-55 to 125	20 Ld PDIP	E20.3
CD74HC573E	-55 to 125	20 Ld PDIP	E20.3
CD74HCT573E	-55 to 125	20 Ld PDIP	E20.3
CD74HC373M	-55 to 125	20 Ld SOIC	M20.3
CD74HCT373M	-55 to 125	20 Ld SOIC	M20.3
CD74HC573M	-55 to 125	20 Ld SOIC	M20.3
CD74HCT573M	-55 to 125	20 Ld SOIC	M20.3

NOTES:

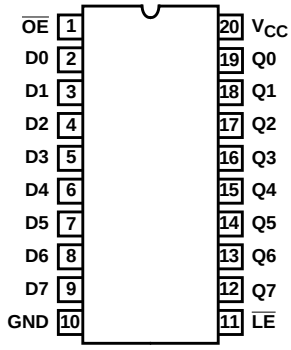
1. When ordering, use the entire part number. Add the suffix 96 to obtain the variant in the tape and reel.
2. Wafer or die for this part number are available which meets all electrical specifications. Please contact your local sales office or Harris customer service for ordering information.

Pinout

CD74HC373, CD74HCT373
(PDIP, SOIC)
TOP VIEW

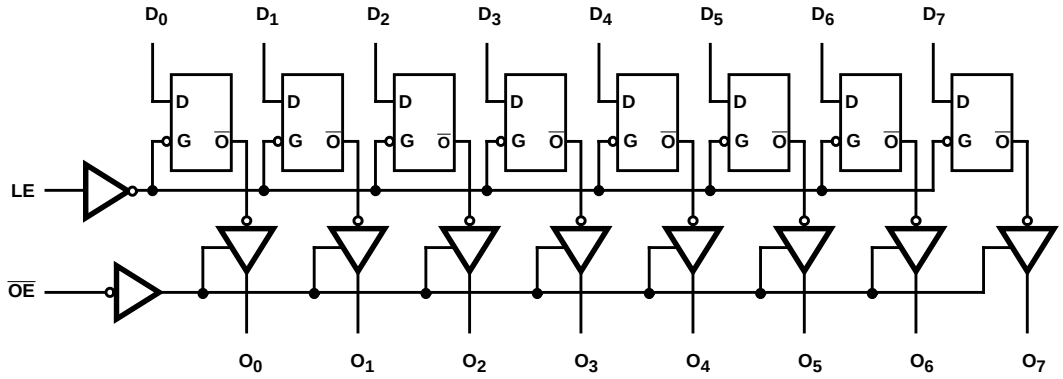


CD54HC573, CD74HC573, CD74HCT573
(PDIP, SOIC, CERDIP)
TOP VIEW

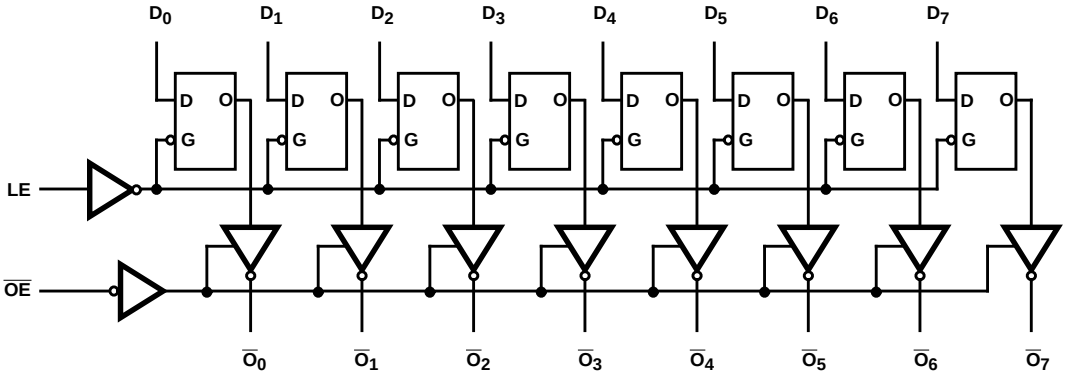


Functional Block Diagrams

CD74HC373, CD74HCT373, CD74HC573, CD74HCT573



CD74HCT573



TRUTH TABLE

$\overline{\text{OUTPUT ENABLE}}$	$\overline{\text{LATCH ENABLE}}$	DATA	OUTPUT
L	H	H	H
L	H	L	L
L	L	l	L
L	L	h	H
H	X	X	Z

NOTE: H = High Voltage Level, L = Low Voltage Level, X = Don't Care, Z = High Impedance State, l = Low voltage level one set-up time prior to the high to low latch enable transition, h = High voltage level one set-up time prior to the high to low latch enable transition.

Absolute Maximum Ratings

DC Supply Voltage, V_{CC} . . . . . -0.5V to 7V
DC Input Diode Current, I_{IK}
For V_I < -0.5V or V_I > V_{CC} + 0.5V . . . . . ±20mA
DC Output Diode Current, I_{OK}
For V_O < -0.5V or V_O > V_{CC} + 0.5V . . . . . ±20mA
DC Drain Current, per Output, I_O
For -0.5V < V_O < V_{CC} + 0.5V . . . . . ±35mA
DC Output Source or Sink Current per Output Pin, I_O
For V_O > -0.5V or V_O < V_{CC} + 0.5V . . . . . ±25mA
DC V_{CC} or Ground Current, I_{CC} . . . . . ±50mA

Operating Conditions

Temperature Range, T_A . . . . . -55°C to 125°C
Supply Voltage Range, V_{CC}
HC Types . . . . . 2V to 6V
HCT Types . . . . . 4.5V to 5.5V
DC Input or Output Voltage, V_I, V_O . . . . . 0V to V_{CC}
Input Rise and Fall Time
2V . . . . . 1000ns (Max)
4.5V. . . . . 500ns (Max)
6V . . . . . 400ns (Max)

Thermal Information

Thermal Resistance (Typical, Note 3)	θ_{JA} (°C/W)	θ_{JA} (°C/W)
PDIP Package	125	N/A
CERDIP Package	85	24
SOIC Package	120	N/A

Maximum Junction Temperature (Plastic Package) . . . . . 150°C
Maximum Storage Temperature Range . . . . . -65°C to 150°C
Maximum Lead Temperature (Soldering 10s) . . . . . 300°C
(SOIC - Lead Tips Only)

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

NOTE:

3. θ_{JA} is measured with the component mounted on an evaluation PC board in free air.

DC Electrical Specifications

PARAMETER	SYMBOL	TEST CONDITIONS		V_{CC} (V)	25°C			-40°C TO 85°C		-55°C TO 125°C		UNITS
		V_I (V)	I_O (mA)		MIN	TYP	MAX	MIN	MAX	MIN	MAX	
HC TYPES												
High Level Input Voltage	V_{IH}	-	-	2	1.5	-	-	1.5	-	1.5	-	V
				4.5	3.15	-	-	3.15	-	3.15	-	V
				6	4.2	-	-	4.2	-	4.2	-	V
Low Level Input Voltage	V_{IL}	-	-	2	-	-	0.5	-	0.5	-	0.5	V
				4.5	-	-	1.35	-	1.35	-	1.35	V
				6	-	-	1.8	-	1.8	-	1.8	V
High Level Output Voltage CMOS Loads	V_{OH}	V_{IH} or V_{IL}	-0.02	2	1.9	-	-	1.9	-	1.9	-	V
			-0.02	4.5	4.4	-	-	4.4	-	4.4	-	V
			-0.02	6	5.9	-	-	5.9	-	5.9	-	V
High Level Output Voltage TTL Loads			-6	4.5	3.98	-	-	3.84	-	3.7	-	V
			-7.8	6	5.48	-	-	5.34	-	5.2	-	V
Low Level Output Voltage CMOS Loads	V_{OL}	V_{IH} or V_{IL}	0.02	2	-	-	0.1	-	0.1	-	0.1	V
			0.02	4.5	-	-	0.1	-	0.1	-	0.1	V
			0.02	6	-	-	0.1	-	0.1	-	0.1	V
Low Level Output Voltage TTL Loads			6	4.5	-	-	0.26	-	0.33	-	0.4	V
			7.8	6	-	-	0.26	-	0.33	-	0.4	V
Input Leakage Current	I_I	V_{CC} or GND	-	6	-	-	±0.1	-	±1	-	±1	µA
Quiescent Device Current	I_{CC}	V_{CC} or GND	0	6	-	-	8	-	80	-	160	µA

DC Electrical Specifications (Continued)

PARAMETER	SYMBOL	TEST CONDITIONS		V_{CC} (V)	25°C			-40°C TO 85°C		-55°C TO 125°C		UNITS
		V_I (V)	I_O (mA)		MIN	TYP	MAX	MIN	MAX	MIN	MAX	
Three-State Leakage Current	-	V_{IL} or V_{IH}	V_O = V_{CC} or GND	6	-	-	±0.5	-	±5	-	±10	µA
HCT TYPES												
High Level Input Voltage	V_{IH}	-	-	4.5 to 5.5	2	-	-	2	-	2	-	V
Low Level Input Voltage	V_{IL}	-	-	4.5 to 5.5	-	-	0.8	-	0.8	-	0.8	V
High Level Output Voltage CMOS Loads	V_{OH}	V_{IH} or V_{IL}	-0.02	4.5	4.4	-	-	4.4	-	4.4	-	V
High Level Output Voltage TTL Loads			-6	4.5	3.98	-	-	3.84	-	3.7	-	V
			-7.8	6	5.48	-	-	5.34	-	5.2	-	V
Low Level Output Voltage CMOS Loads	V_{OL}	V_{IH} or V_{IL}	0.02	4.5	-	-	0.1	-	0.1	-	0.1	V
Low Level Output Voltage TTL Loads			6	4.5	-	-	0.26	-	0.33	-	0.4	V
			7.8	6	-	-	0.26	-	0.33	-	0.4	V
Input Leakage Current	I_I	V_{CC} to GND	-	5.5	-	-	±0.1	-	±1	-	±1	µA
Quiescent Device Current	I_{CC}	V_{CC} or GND	0	5.5	-	-	8	-	80	-	160	µA
Three-State Leakage Current	-	V_{IL} or V_{IH}	V_O = V_{CC} or GND	6	-	-	±0.5	-	±5	-	±10	µA
Additional Quiescent Device Current Per Input Pin: 1 Unit Load (Note 4)	ΔI_{CC}	V_{CC} -2.1	-	4.5 to 5.5	-	100	360	-	450	-	490	µA

NOTE:

4. For dual-supply systems theoretical worst case (V_I = 2.4V, V_{CC} = 5.5V) specification is 1.8mA.

HCT Input Loading Table

INPUT	UNIT LOADS	
	HCT373	HCT573
$\overline{OE}$	1.5	1.25
Dn	0.4	0.3
$\overline{LE}$	0.6	0.65

NOTE: Unit Load is ΔI_{CC} limit specified in DC Electrical Specifications table, e.g., 360µA max at 25°C.

Prerequisite For Switching Specifications

PARAMETER	SYMBOL	TEST CONDITIONS	V_{CC} (V)	25°C			-40°C TO 85°C		-55°C TO 125°C		UNITS
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
HC TYPES											
$\overline{LE}$ Pulse Width	t_W	-	2	80	-	-	100	-	120	-	ns
			4.5	16	-	-	20	-	24	-	ns
			6	14	-	-	17	-	20	-	ns
Set-up Time Data to $\overline{LE}$	t_{SU}	-	2	50	-	-	65	-	75	-	ns
			4.5	10	-	-	13	-	15	-	ns
			6	9	-	-	11	-	13	-	ns
Hold Time, Data to $\overline{LE}$ (573)	t_H	-	2	40	-	-	50	-	60	-	ns
			4.5	8	-	-	10	-	12	-	ns
			6	7	-	-	9	-	10	-	ns
Hold Time, Data to $\overline{LE}$ (373)	t_H	-	2	5	-	-	5	-	5	-	ns
			4.5	5	-	-	5	-	5	-	ns
			6	5	-	-	5	-	5	-	ns
HCT TYPES											
$\overline{LE}$ Pulse Width	t_w	-	4.5	16	-	-	20	-	24	-	ns
Set-up Time Data to $\overline{LE}$	t_w	-	4.5	13	-	-	16	-	20	-	ns
Hold Time, Data to $\overline{LE}$	t_H	-	4.5	10	-	-	13	-	15	-	ns

Switching Specifications Input t_r, t_f = 6ns

PARAMETER	SYMBOL	TEST CONDITIONS	V_{CC} (V)	25°C		-40°C TO 85°C	-55°C TO 125°C	UNITS
				TYP	MAX	MAX	MAX	
HC TYPES								
Propagation Delay, Data to Qn (HC/HCT373)	t_{PLH}, t_{PHL}	C_L = 50pF	2	-	150	190	225	ns
			4.5	-	30	38	45	ns
			6	-	26	33	38	ns
		C_L = 15pF	5	12	-	-	-	ns
Propagation Delay, Data to Qn (HC/HCT573)	t_{PLH}, t_{PHL}	C_L = 50pF	2	-	175	220	265	ns
			4.5	-	35	44	53	ns
			6	-	30	37	45	ns
		C_L = 15pF	5	14	-	-	-	ns
Propagation Delay, $\overline{LE}$ to Qn	t_{PLH}, t_{PHL}	C_L = 50pF	2	-	175	220	265	ns
			4.5	-	35	44	53	ns
			6	-	30	37	45	ns
		C_L = 15pF	5	14	-	-	-	ns

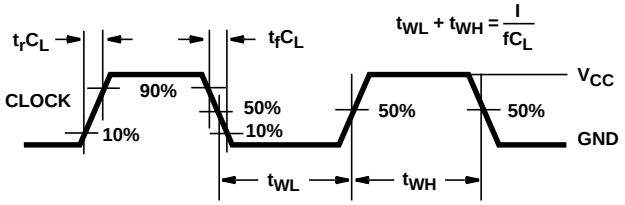
Switching Specifications Input t_r, t_f = 6ns **(Continued)**

PARAMETER	SYMBOL	TEST CONDITIONS	V_{CC} (V)	25°C		-40°C TO 85°C	-55°C TO 125°C	UNITS
				TYP	MAX	MAX	MAX	
Output Enabling Time	t_{PZL}, t_{PZH}	C_L = 50pF	2	-	150	190	225	ns
			4.5	-	30	38	45	ns
			6	-	26	33	38	ns
		C_L = 15pF	5	12	-	-	-	ns
Output Disabling Time	t_{PLZ}, t_{PHZ}	C_L = 50pF	2	-	150	190	225	ns
			4.5	-	30	38	45	ns
			6	-	26	33	38	ns
		C_L = 15pF	5	12	-	-	-	ns
Output Transition Time	t_{TLH}, t_{THL}	C_L = 50pF	2	-	60	75	90	ns
			4.5	-	12	15	18	ns
			6	-	10	13	15	ns
Input Capacitance	C_I	-	-	-	10	10	10	pF
Three-State Output Capacitance	C_O	-	-	-	20	20	20	pF
Power Dissipation Capacitance (Notes 5, 6)	C_{PD}	-	5	51	-	-	-	pF
HCT TYPES								
Propagation Delay, Data to Qn (HC/HCT373)	t_{PLH}, t_{PHL}	C_L = 50pF	4.5	-	32	40	48	ns
		C_L = 15pF	5	13	-	-	-	ns
Propagation Delay, Data to Qn (HC/HCT573)	t_{PLH}, t_{PHL}	C_L = 50pF	4.5	-	35	44	53	ns
		C_L = 15pF	5	17	-	-	-	ns
Propagation Delay, $\overline{LE}$ to Qn	t_{PLH}, t_{PHL}	C_L = 50pF	4.5	-	35	44	53	ns
		C_L = 15pF	5	14	-	-	-	ns
Output Enabling Time	t_{PZL}, t_{PZH}	C_L = 50pF	4.5	-	35	44	53	ns
		C_L = 15pF	5	14	-	-	-	ns
Output Disabling Time	t_{PLZ}, t_{PZH}	C_L = 50pF	4.5	-	35	44	53	ns
		C_L = 15pF	5	14	-	-	-	ns
Output Transition Time	t_{TLH}, t_{THL}	C_L = 50pF	4.5	-	12	15	18	ns
Input Capacitance	C_I	-	-	-	10	10	10	pF
Three-State Output Capacitance	C_O	-	-	-	20	20	20	pF
Power Dissipation Capacitance (Notes 5, 6)	C_{PD}	-	5	53	-	-	-	pF

NOTES:

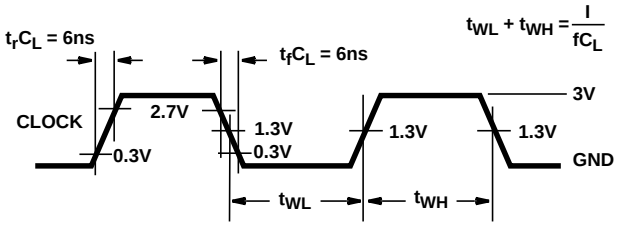
5. C_{PD} is used to determine the no-load dynamic power consumption, per latch.
6. P_D (total power per latch) = V_{CC}^2 f_i (C_{PD} + C_L) where f_i = Input Frequency, C_L = Output Load Capacitance, V_{CC} = Supply Voltage.

Test Circuits and Waveforms



NOTE: Outputs should be switching from 10% V_{CC} to 90% V_{CC} in accordance with device truth table. For f_{MAX}, input duty cycle = 50%.

FIGURE 1. HC CLOCK PULSE RISE AND FALL TIMES AND PULSE WIDTH



NOTE: Outputs should be switching from 10% V_{CC} to 90% V_{CC} in accordance with device truth table. For f_{MAX}, input duty cycle = 50%.

FIGURE 2. HCT CLOCK PULSE RISE AND FALL TIMES AND PULSE WIDTH

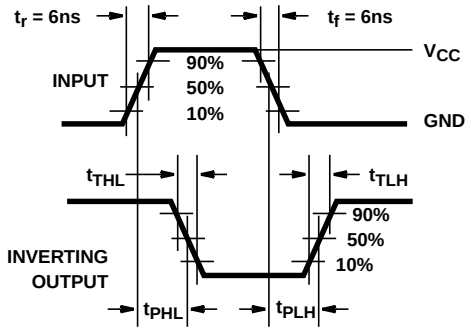


FIGURE 3. HC TRANSITION TIMES AND PROPAGATION DELAY TIMES, COMBINATION LOGIC

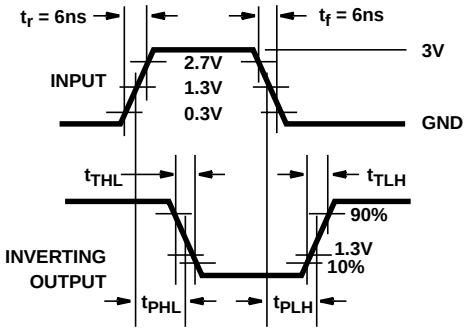


FIGURE 4. HCT TRANSITION TIMES AND PROPAGATION DELAY TIMES, COMBINATION LOGIC

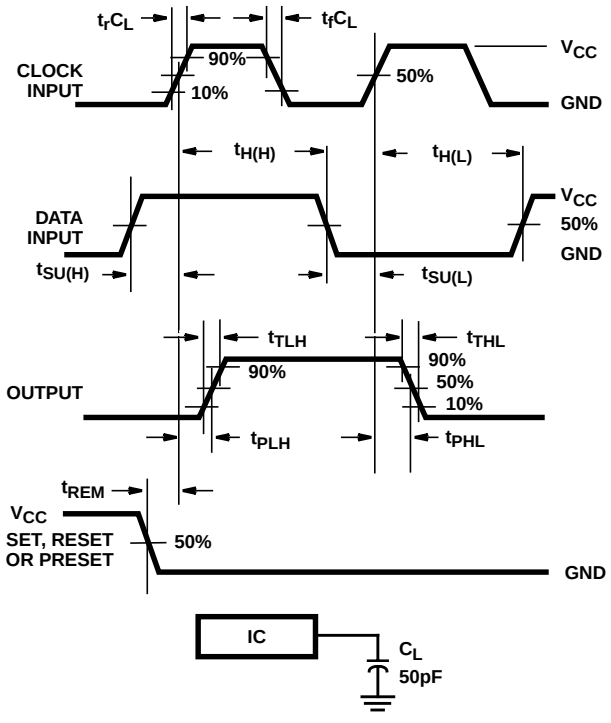


FIGURE 5. HC SETUP TIMES, HOLD TIMES, REMOVAL TIME, AND PROPAGATION DELAY TIMES FOR EDGE TRIGGERED SEQUENTIAL LOGIC CIRCUITS

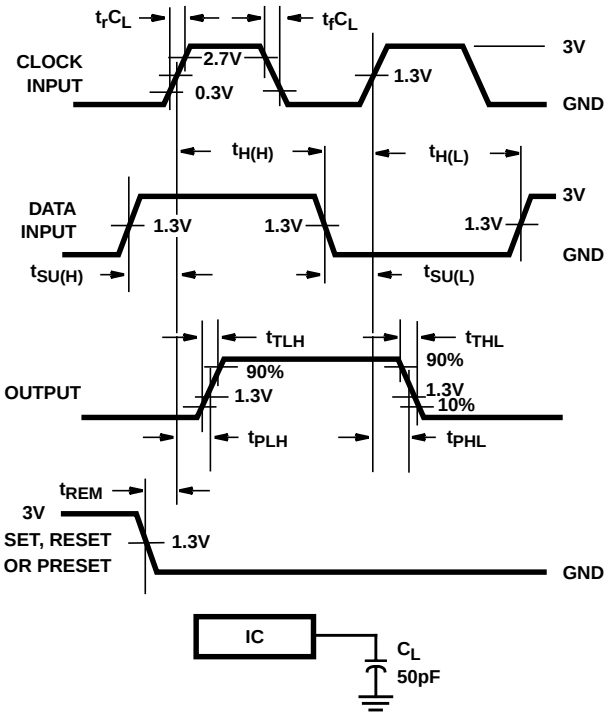


FIGURE 6. HCT SETUP TIMES, HOLD TIMES, REMOVAL TIME, AND PROPAGATION DELAY TIMES FOR EDGE TRIGGERED SEQUENTIAL LOGIC CIRCUITS

Test Circuits and Waveforms (Continued)

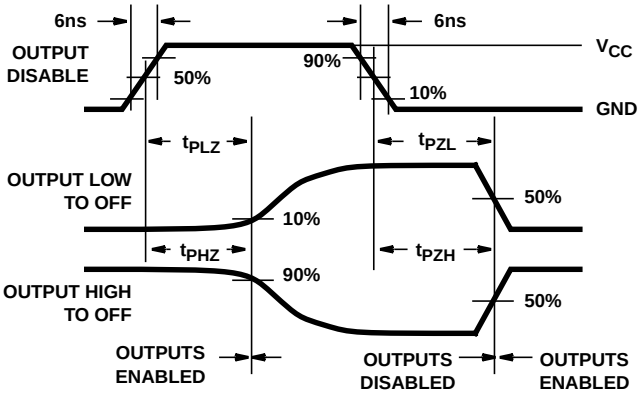


FIGURE 7. HC THREE-STATE PROPAGATION DELAY WAVEFORM

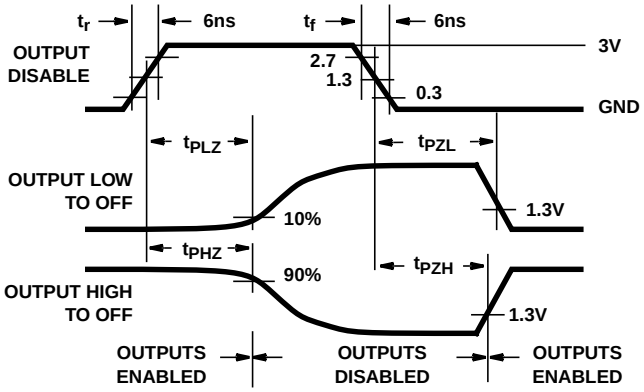
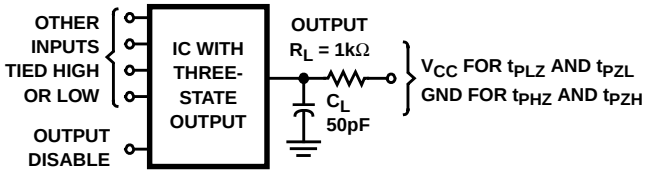


FIGURE 8. HCT THREE-STATE PROPAGATION DELAY WAVEFORM



NOTE: Open drain waveforms t_{PLZ} and t_{PZL} are the same as those for three-state shown on the left. The test circuit is Output R_L = 1kΩ to V_{CC}, C_L = 50pF.

FIGURE 9. HC AND HCT THREE-STATE PROPAGATION DELAY TEST CIRCUIT

IMPORTANT NOTICE

Texas Instruments and its subsidiaries (TI) reserve the right to make changes to their products or to discontinue any product or service without notice, and advise customers to obtain the latest version of relevant information to verify, before placing orders, that information being relied on is current and complete. All products are sold subject to the terms and conditions of sale supplied at the time of order acknowledgement, including those pertaining to warranty, patent infringement, and limitation of liability.

TI warrants performance of its semiconductor products to the specifications applicable at the time of sale in accordance with TI's standard warranty. Testing and other quality control techniques are utilized to the extent TI deems necessary to support this warranty. Specific testing of all parameters of each device is not necessarily performed, except those mandated by government requirements.

CERTAIN APPLICATIONS USING SEMICONDUCTOR PRODUCTS MAY INVOLVE POTENTIAL RISKS OF DEATH, PERSONAL INJURY, OR SEVERE PROPERTY OR ENVIRONMENTAL DAMAGE ("CRITICAL APPLICATIONS"). TI SEMICONDUCTOR PRODUCTS ARE NOT DESIGNED, AUTHORIZED, OR WARRANTED TO BE SUITABLE FOR USE IN LIFE-SUPPORT DEVICES OR SYSTEMS OR OTHER CRITICAL APPLICATIONS. INCLUSION OF TI PRODUCTS IN SUCH APPLICATIONS IS UNDERSTOOD TO BE FULLY AT THE CUSTOMER'S RISK.

In order to minimize risks associated with the customer's applications, adequate design and operating safeguards must be provided by the customer to minimize inherent or procedural hazards.

TI assumes no liability for applications assistance or customer product design. TI does not warrant or represent that any license, either express or implied, is granted under any patent right, copyright, mask work right, or other intellectual property right of TI covering or relating to any combination, machine, or process in which such semiconductor products or services might be or are used. TI's publication of information regarding any third party's products or services does not constitute TI's approval, warranty or endorsement thereof.